Intel - EPF10K10TC144-4N Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	72
Number of Logic Elements/Cells	576
Total RAM Bits	6144
Number of I/O	102
Number of Gates	31000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k10tc144-4n

Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

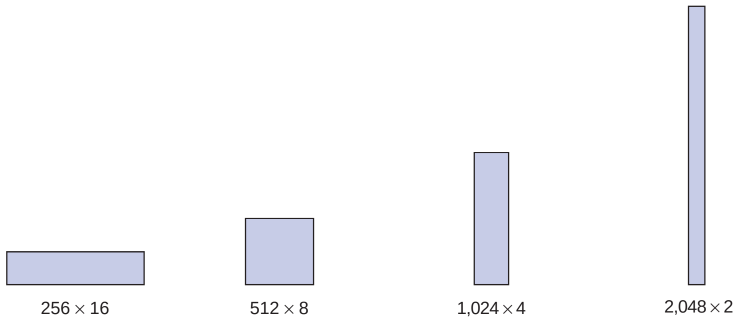
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions such as LPM functions can take advantage of the EAB automatically.

The FLEX 10KE EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These small FPGA RAM blocks must be connected together to make RAM blocks of manageable size. The RAM blocks are connected together using multiplexers implemented with more logic blocks. These extra multiplexers cause extra delay, which slows down the RAM block. FPGA RAM blocks are also prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

The FLEX 10KE enhanced EAB adds dual-port capability to the existing EAB structure. The dual-port structure is ideal for FIFO buffers with one or two clocks. The FLEX 10KE EAB can also support up to 16-bit-wide RAM blocks and is backward-compatible with any design containing FLEX 10K EABs. The FLEX 10KE EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, which allows the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.

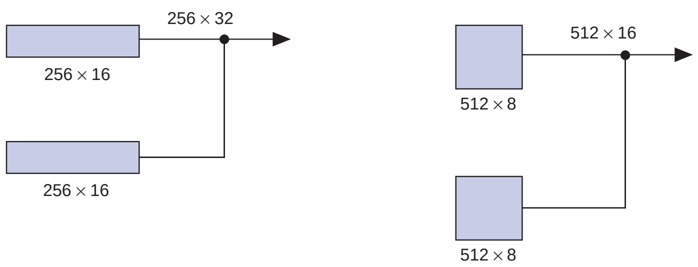
When used as RAM, each EAB can be configured in any of the following sizes: 256 × 16, 512 × 8, 1,024 × 4, or 2,048 × 2 (see Figure 5).

Figure 5. FLEX 10KE EAB Memory Configurations



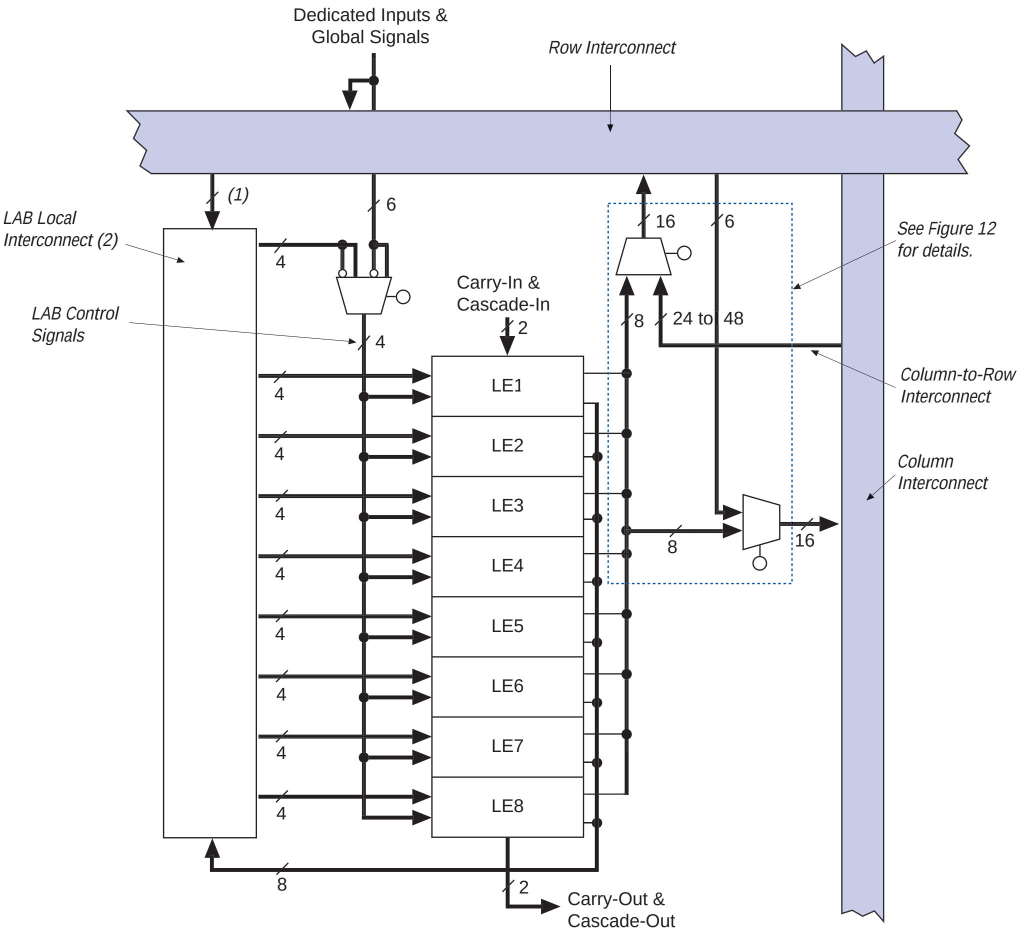
Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 16 RAM blocks can be combined to form a 256 × 32 block; two 512 × 8 RAM blocks can be combined to form a 512 × 16 block (see Figure 6).

Figure 6. Examples of Combining FLEX 10KE EABs



If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. The Altera software automatically combines EABs to meet a designer's RAM specifications.

Figure 7. FLEX 10KE LAB



Notes:

(1) EPF10K30E, EPF10K50E, and EPF10K50S devices have 22 inputs to the LAB local interconnect channel from the row; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 26.

(2) EPF10K30E, EPF10K50E, and EPF10K50S devices have 30 LAB local interconnect channels; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 34.

The programmable flipflop in the LE can be configured for D, T, JK, or SR operation. The clock, clear, and preset control signals on the flipflop can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the flipflop is bypassed and the output of the LUT drives the output of the LE.

The LE has two outputs that drive the interconnect: one drives the local interconnect and the other drives either the row or column FastTrack Interconnect routing structure. The two outputs can be controlled independently. For example, the LUT can drive one output while the register drives the other output. This feature, called register packing, can improve LE utilization because the register and the LUT can be used for unrelated functions.

The FLEX 10KE architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. The carry chain supports high-speed counters and adders and the cascade chain implements wide-input functions with minimum delay. Carry and cascade chains connect all LEs in a LAB as well as all LABs in the same row. Intensive use of carry and cascade chains can reduce routing flexibility. Therefore, the use of these chains should be limited to speed-critical portions of a design.

Carry Chain

The carry chain provides a very fast (as low as 0.2 ns) carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the FLEX 10KE architecture to implement high-speed counters, adders, and comparators of arbitrary width efficiently. Carry chain logic can be created automatically by the Altera Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as LPM and DesignWare functions automatically take advantage of carry chains.

Carry chains longer than eight LEs are automatically implemented by linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a row. A carry chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB. For example, the last LE of the first LAB in a row carries to the first LE of the third LAB in the row. The carry chain does not cross the EAB at the middle of the row. For instance, in the EPF10K50E device, the carry chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB.

FastTrack Interconnect Routing Structure

In the FLEX 10KE architecture, connections between LEs, EABs, and device I/O pins are provided by the FastTrack Interconnect routing structure, which is a series of continuous horizontal and vertical routing channels that traverses the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

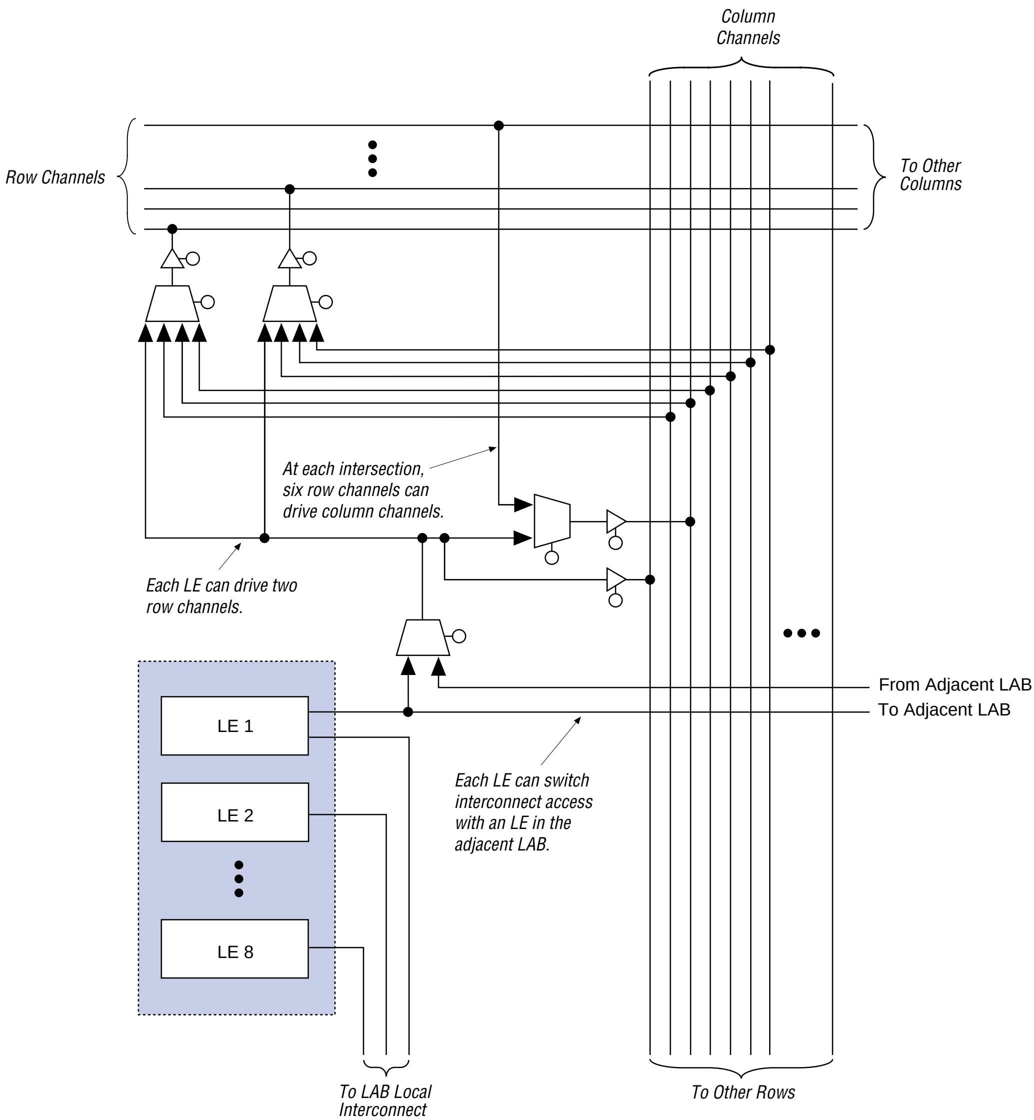
The FastTrack Interconnect routing structure consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the row. The column interconnect routes signals between rows and can drive I/O pins.

Row channels drive into the LAB or EAB local interconnect. The row signal is buffered at every LAB or EAB to reduce the effect of fan-out on delay. A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in a LAB drive the row interconnect.

Each column of LABs or EABs is served by a dedicated column interconnect. The column interconnect that serves the EABs has twice as many channels as other column interconnects. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs or EABs in the device. A signal from the column interconnect, which can be either the output of a LE or an input from an I/O pin, must be routed to the row interconnect before it can enter a LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, a LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This flexibility enables routing resources to be used more efficiently (see Figure 13).

Figure 13. FLEX 10KE LAB Connections to Row & Column Interconnect



When dedicated inputs drive non-inverted and inverted peripheral clears, clock enables, and output enables, two signals on the peripheral control bus will be used.

Tables 8 and 9 list the sources for each peripheral control signal, and show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals. The tables also show the rows that can drive global signals.

Table 8. Peripheral Bus Sources for EPF10K30E, EPF10K50E & EPF10K50S Devices

Peripheral Control Signal	EPF10K30E	EPF10K50E EPF10K50S
OE0	Row A	Row A
OE1	Row B	Row B
OE2	Row C	Row D
OE3	Row D	Row F
OE4	Row E	Row H
OE5	Row F	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A
CLKENA1/OE6/GLOBAL1	Row B	Row C
CLKENA2/CLR0	Row C	Row E
CLKENA3/OE7/GLOBAL2	Row D	Row G
CLKENA4/CLR1	Row E	Row I
CLKENA5/CLK1/GLOBAL3	Row F	Row J

Tables 12 and 13 summarize the ClockLock and ClockBoost parameters for -1 and -2 speed-grade devices, respectively.

Table 12. ClockLock & ClockBoost Parameters for -1 Speed-Grade Devices

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_R	Input rise time				5	ns
t_F	Input fall time				5	ns
t_{INDUTY}	Input duty cycle		40		60	%
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)		25		180	MHz
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)		16		90	MHz
f_{CLKDEV}	Input deviation from user specification in the MAX+PLUS II software *(1)*				25,000 *(2)*	PPM
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)				100	ps
t_{LOCK}	Time required for ClockLock or ClockBoost to acquire lock *(3)*				10	µs
t_{JITTER}	Jitter on ClockLock or ClockBoost-generated clock *(4)*	$t_{INCLKSTB}$ < 100			250	ps
		$t_{INCLKSTB}$ < 50			200 *(4)*	ps
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock		40	50	60	%

Table 20. 2.5-V EPF10K50E & EPF10K200E Device Recommended Operating Conditions					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	2.30 (2.30)	2.70 (2.70)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.30 (2.30)	2.70 (2.70)	V
V_I	Input voltage	*(5)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 21. 2.5-V EPF10K30E, EPF10K50S, EPF10K100E, EPF10K130E & EPF10K200S Device Recommended Operating Conditions					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	*(5)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 27. EAB Timing Macroparameters Note (1), (6)		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB `WE` setup time before clock when using input register	
t_{EABWEH}	EAB `WE` hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Table 28. Interconnect Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{DIN2IOE}$	Delay from dedicated input pin to IOE control input	*(7)*
t_{DIN2LE}	Delay from dedicated input pin to LE or EAB control input	*(7)*
$t_{DCLK2IOE}$	Delay from dedicated clock pin to IOE clock	*(7)*
$t_{DCLK2LE}$	Delay from dedicated clock pin to LE or EAB clock	*(7)*
$t_{DIN2DATA}$	Delay from dedicated input or clock to LE or EAB data	*(7)*
$t_{SAMELAB}$	Routing delay for an LE driving another LE in the same LAB	
$t_{SAMEROW}$	Routing delay for a row IOE, LE, or EAB driving a row IOE, LE, or EAB in the same row	*(7)*
$t_{SAMECOLUMN}$	Routing delay for an LE driving an IOE in the same column	*(7)*
$t_{DIFFROW}$	Routing delay for a column IOE, LE, or EAB driving an LE or EAB in a different row	*(7)*
$t_{TWOROWS}$	Routing delay for a row IOE or EAB driving an LE or EAB in a different row	*(7)*
$t_{LEPERIPH}$	Routing delay for an LE driving a control signal of an IOE via the peripheral control bus	*(7)*
$t_{LABCARRY}$	Routing delay for the carry-out signal of an LE driving the carry-in signal of a different LE in a different LAB	
$t_{LABCASC}$	Routing delay for the cascade-out signal of an LE driving the cascade-in signal of a different LE in a different LAB	

Table 29. External Timing Parameters

Symbol	Parameter	Conditions
t_{DRR}	Register-to-register delay via four LEs, three row interconnects, and four local interconnects	*(8)*
t_{INSU}	Setup time with global clock at IOE register	*(9)*
t_{INH}	Hold time with global clock at IOE register	*(9)*
t_{OUTCO}	Clock-to-output delay with global clock at IOE register	*(9)*
t_{PCISU}	Setup time with global clock for registers used in PCI designs	*(9)*,*(10)*
t_{PCIH}	Hold time with global clock for registers used in PCI designs	*(9)*,*(10)*
t_{PCICO}	Clock-to-output delay with global clock for registers used in PCI designs	*(9)*,*(10)*

Table 38. EPF10K50E Device LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_H	0.9		1.0		1.4		ns
t_{PRE}		0.5		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 39. EPF10K50E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.2		2.4		3.3	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		1.0		1.0		1.4	ns
t_{IOCOMB}		0.0		0.0		0.2	ns
t_{IOSU}	1.0		1.2		1.7		ns
t_{IOH}	0.3		0.3		0.5		ns
t_{IOCLR}		0.9		1.0		1.4	ns
t_{OD1}		0.8		0.9		1.2	ns
t_{OD2}		0.3		0.4		0.7	ns
t_{OD3}		3.0		3.5		3.5	ns
t_{XZ}		1.4		1.7		2.3	ns
t_{ZX1}		1.4		1.7		2.3	ns
t_{ZX2}		0.9		1.2		1.8	ns
t_{ZX3}		3.6		4.3		4.6	ns
t_{INREG}		4.9		5.8		7.8	ns
t_{IOFD}		2.8		3.3		4.5	ns
t_{INCOMB}		2.8		3.3		4.5	ns

Table 41. EPF10K50E Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.4		7.6		10.2	ns
$t_{EABRCOMB}$	6.4		7.6		10.2		ns
$t_{EABRCREG}$	4.4		5.1		7.0		ns
t_{EABWP}	2.5		2.9		3.9		ns
$t_{EABWCOMB}$	6.0		7.0		9.5		ns
$t_{EABWCREG}$	6.8		7.8		10.6		ns
t_{EABDD}		5.7		6.7		9.0	ns
$t_{EABDATACO}$		0.8		0.9		1.3	ns
$t_{EABDATASU}$	1.5		1.7		2.3		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	1.3		1.4		2.0		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.5		1.7		2.3		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.8		ns
t_{EABWAH}	0.5		0.5		0.8		ns
t_{EABWO}		5.1		6.0		8.1	ns

Table 42. EPF10K50E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.5		4.3		5.6	ns
t_{DIN2LE}		2.1		2.5		3.4	ns
$t_{DIN2DATA}$		2.2		2.4		3.1	ns
$t_{DCLK2IOE}$		2.9		3.5		4.7	ns
$t_{DCLK2LE}$		2.1		2.5		3.4	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.1		1.1		1.5	ns
$t_{SAMECOLUMN}$		0.8		1.0		1.3	ns
$t_{DIFFROW}$		1.9		2.1		2.8	ns
$t_{TWOROWS}$		3.0		3.2		4.3	ns
$t_{LEPERIPH}$		3.1		3.3		3.7	ns
$t_{LABCARRY}$		0.1		0.1		0.2	ns
$t_{LABCASC}$		0.3		0.3		0.5	ns

Table 43. EPF10K50E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		8.5		10.0		13.5	ns
t_{INSU}	2.7		3.2		4.3		ns
t_{INH}	0.0		0.0		0.0		ns
t_{OUTCO}	2.0	4.5	2.0	5.2	2.0	7.3	ns
t_{PCISU}	3.0		4.2		-		ns
t_{PCIH}	0.0		0.0		-		ns
t_{PCICO}	2.0	6.0	2.0	7.7	-	-	ns

Table 44. EPF10K50E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.7		3.2		4.3		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	4.5	2.0	5.2	2.0	7.3	ns
$t_{XZBIDIR}$		6.8		7.8		10.1	ns
$t_{ZXBIDIR}$		6.8		7.8		10.1	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.

Tables 45 through 51 show EPF10K100E device internal and external timing parameters.

Table 45. EPF10K100E Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		1.0		1.5	ns
t_{CLUT}		0.5		0.7		0.9	ns
t_{RLUT}		0.6		0.8		1.1	ns
t_{PACKED}		0.3		0.4		0.5	ns
t_{EN}		0.2		0.3		0.3	ns
t_{CICO}		0.1		0.1		0.2	ns
t_{CGEN}		0.4		0.5		0.7	ns

Tables 52 through 58 show EPF10K130E device internal and external timing parameters.

Table 52. EPF10K130E Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.9		1.3	ns
t_{CLUT}		0.6		0.8		1.0	ns
t_{RLUT}		0.7		0.9		0.2	ns
t_{PACKED}		0.3		0.5		0.6	ns
t_{EN}		0.2		0.3		0.4	ns
t_{CICO}		0.1		0.1		0.2	ns
t_{CGEN}		0.4		0.6		0.8	ns
t_{CGENR}		0.1		0.1		0.2	ns
t_{CASC}		0.6		0.9		1.2	ns
t_{C}		0.3		0.5		0.6	ns
t_{CO}		0.5		0.7		0.8	ns
t_{COMB}		0.3		0.5		0.6	ns
t_{SU}	0.5		0.7		0.8		ns
t_{H}	0.6		0.7		1.0		ns
t_{PRE}		0.9		1.2		1.6	ns
t_{CLR}		0.9		1.2		1.6	ns
t_{CH}	1.5		1.5		2.5		ns
t_{CL}	1.5		1.5		2.5		ns

Table 53. EPF10K130E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.3		1.5		2.0	ns
t_{IOC}		0.0		0.0		0.0	ns
t_{IOCO}		0.6		0.8		1.0	ns
t_{IOCOMB}		0.6		0.8		1.0	ns
t_{IOSU}	1.0		1.2		1.6		ns
t_{IOH}	0.9		0.9		1.4		ns
t_{IOCLR}		0.6		0.8		1.0	ns
t_{OD1}		2.8		4.1		5.5	ns
t_{OD2}		2.8		4.1		5.5	ns

Table 56. EPF10K130E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		2.8		3.5		4.4	ns
t_{DIN2LE}		0.7		1.2		1.6	ns
$t_{DIN2DATA}$		1.6		1.9		2.2	ns
$t_{DCLK2IOE}$		1.6		2.1		2.7	ns
$t_{DCLK2LE}$		0.7		1.2		1.6	ns
$t_{SAMELAB}$		0.1		0.2		0.2	ns
$t_{SAMEROW}$		1.9		3.4		5.1	ns
$t_{SAMECOLUMN}$		0.9		2.6		4.4	ns
$t_{DIFFROW}$		2.8		6.0		9.5	ns
$t_{TWOROWS}$		4.7		9.4		14.6	ns
$t_{LEPERIPH}$		3.1		4.7		6.9	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.9		1.2		1.6	ns

Table 57. EPF10K130E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	1.9		2.1		3.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.0	2.0	7.0	2.0	9.2	ns
t_{INSU} *(4)*	0.9		1.1		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	4.0	0.5	6.0	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 59. EPF10K200E Device LE Timing Microparameters *(Part 2 of 2)* *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_H	0.9		1.1		1.5		ns
t_{PRE}		0.5		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 60. EPF10K200E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.6		1.9		2.6	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		1.6		1.9		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		0.9		1.2		ns
t_{IOH}	0.7		0.8		1.1		ns
t_{IOCLR}		0.2		0.2		0.3	ns
t_{OD1}		0.6		0.7		0.9	ns
t_{OD2}		0.1		0.2		0.7	ns
t_{OD3}		2.5		3.0		3.9	ns
t_{XZ}		4.4		5.3		7.1	ns
t_{ZX1}		4.4		5.3		7.1	ns
t_{ZX2}		3.9		4.8		6.9	ns
t_{ZX3}		6.3		7.6		10.1	ns
t_{INREG}		4.8		5.7		7.7	ns
t_{IOFD}		1.5		1.8		2.4	ns
t_{INCOMB}		1.5		1.8		2.4	ns

Table 66. EPF10K50S Device LE Timing Microparameters (Part 2 of 2) *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{CGENR}		0.1		0.1		0.1	ns
t_{CASC}		0.5		0.8		1.0	ns
t_C		0.5		0.6		0.8	ns
t_{CO}		0.6		0.6		0.7	ns
t_{COMB}		0.3		0.4		0.5	ns
t_{SU}	0.5		0.6		0.7		ns
t_H	0.5		0.6		0.8		ns
t_{PRE}		0.4		0.5		0.7	ns
t_{CLR}		0.8		1.0		1.2	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 67. EPF10K50S Device IOE Timing Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{IOD}		1.3		1.3		1.9	ns
t_{IOC}		0.3		0.4		0.4	ns
t_{IOCO}		1.7		2.1		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		1.0		1.3		ns
t_{IOH}	0.4		0.5		0.6		ns
t_{IOCLR}		0.2		0.2		0.4	ns
t_{OD1}		1.2		1.2		1.9	ns
t_{OD2}		0.7		0.8		1.7	ns
t_{OD3}		2.7		3.0		4.3	ns
t_{XZ}		4.7		5.7		7.5	ns
t_{ZX1}		4.7		5.7		7.5	ns
t_{ZX2}		4.2		5.3		7.3	ns
t_{ZX3}		6.2		7.5		9.9	ns
t_{INREG}		3.5		4.2		5.6	ns
t_{IOFD}		1.1		1.3		1.8	ns
t_{INCOMB}		1.1		1.3		1.8	ns

Table 73. EPF10K200S Device Internal & External Timing Parameters Note (1)							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{LUT}		0.7		0.8		1.2	ns
t_{CLUT}		0.4		0.5		0.6	ns
t_{RLUT}		0.5		0.7		0.9	ns
t_{PACKED}		0.4		0.5		0.7	ns
t_{EN}		0.6		0.5		0.6	ns
t_{CICO}		0.1		0.2		0.3	ns
t_{CGEN}		0.3		0.4		0.6	ns
t_{CGENR}		0.1		0.2		0.3	ns
t_{CASC}		0.7		0.8		1.2	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.3		0.6		0.8	ns
t_{SU}	0.4		0.6		0.7		ns
t_{H}	1.0		1.1		1.5		ns
t_{PRE}		0.4		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 74. EPF10K200S Device IOE Timing Microparameters (Part 1 of 2) Note (1)							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{IOD}		1.8		1.9		2.6	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		1.7		1.9		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		0.9		1.2		ns
t_{IOH}	0.4		0.8		1.1		ns
t_{IOCLR}		0.2		0.2		0.3	ns
t_{OD1}		1.3		0.7		0.9	ns
t_{OD2}		0.8		0.2		0.4	ns
t_{OD3}		2.9		3.0		3.9	ns
t_{XZ}		5.0		5.3		7.1	ns
t_{ZX1}		5.0		5.3		7.1	ns

Table 77. EPF10K200S Device Interconnect Timing Microparameters (Part 2 of 2) Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{LABCASC}$		0.5		1.0		1.4	ns

Table 78. EPF10K200S External Timing Parameters Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} (2)	3.1		3.7		4.7		ns
t_{INH} (2)	0.0		0.0		0.0		ns
t_{OUTCO} (2)	2.0	3.7	2.0	4.4	2.0	6.3	ns
t_{INSU} (3)	2.1		2.7		–		ns
t_{INH} (3)	0.0		0.0		–		ns
t_{OUTCO} (3)	0.5	2.7	0.5	3.4	–	–	ns
t_{PCISU}	3.0		4.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	8.9	–	–	ns

Table 79. EPF10K200S External Bidirectional Timing Parameters Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (2)	2.3		3.4		4.4		ns
$t_{INHBIDIR}$ (2)	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ (3)	3.3		4.4		–		ns
$t_{INHBIDIR}$ (3)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (2)	2.0	3.7	2.0	4.4	2.0	6.3	ns
$t_{XZBIDIR}$ (2)		6.9		7.6		9.2	ns
$t_{ZXBIDIR}$ (2)		5.9		6.6		–	ns
$t_{OUTCOBIDIR}$ (3)	0.5	2.7	0.5	3.4	–	–	ns
$t_{XZBIDIR}$ (3)		6.9		7.6		9.2	ns
$t_{ZXBIDIR}$ (3)		5.9		6.6		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(3) This parameter is measured with the use of the ClockLock or ClockBoost circuits.